

Ishida, and further in view of Wolf. Applicants respectfully traverse these rejections in view of the amendment because the cited references do not disclose or suggest every element of any claim, as the following analysis shows.

Claim 1 recites depositing a metal layer directly on a top and sides of the alignment component and the region of the substrate adjacent to the alignment component. Support for this limitation may be found in the specification in Figs. 2a, 2b and the descriptive text on page 9 lines 15-19. In paragraph 2 of the Office Action, the rejection cites Rodder, specifically a metal layer 106, as equivalent to the metal layer in the claim. Although item 106 may be comprised of metal (col. 3 lines 9-10), it does not cover the top and sides of the elements 120, 122 (identified in the office action as an alignment component). Rodder specifically teaches against covering the alignment component with item 106 by stating that item 106 is selectively formed adjacent to the alignment component (col. 3 lines 12-14), and Figs. 3A, 3B support this description. The only layer in Rodder that covers the top and sides of the alignment component 120, 122 is layer 114 (Fig. 3C), which is an insulator material (col. 3 line 41), not a metal.

The other cited references do not make up for this missing limitation in Rodder.

The remaining claims all depend, either directly or indirectly, from claim 1 and therefore contain the same limitations not disclosed or suggested by the cited references.

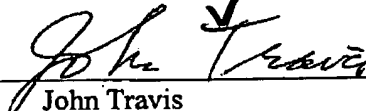
CONCLUSION

For the foregoing reasons, Applicant submits that claims 1-19 and 28-32 are now in condition for allowance, and indication of allowance by the Examiner is respectfully requested. If the Examiner has any questions concerning this application, he or she is requested to telephone the undersigned at the telephone number shown below as soon as possible. If any fee insufficiency or overpayment is discovered, please charge any insufficiency or credit any overpayment to Deposit Account No. 02-2666.

Respectfully submitted,

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APPENDIX A**MARKED UP VERSION OF AMENDED CLAIMS:**

1. (Amended five times) A method of forming a transistor, comprising:

forming an alignment component on a substrate of a semiconductor material, said alignment component consisting of a single material;

depositing a metal layer directly on a top and sides of the alignment component and directly on a region of the substrate adjacent to the alignment component, wherein previous to said depositing the region of the substrate adjacent to the alignment component has not been doped differently than a region of the substrate covered by the alignment component;

reacting the metal layer with the semiconductor material of the substrate to form two silicide regions, the silicide regions having inner surfaces which face one another, wherein an upper portion of each inner surface contacts the alignment component and a lower portion of each inner surface contacts the semiconductor material of the substrate;

removing the alignment component; and

replacing the removed alignment component with a conductive gate.